

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

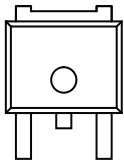
 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

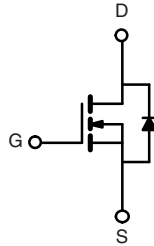
PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.009
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.012
I_D (A)	50
Configuration	Single

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified^d

TO-252

 G D S
Top View

Drain Connected to Tab



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50N03-09-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C ^a	50
		$T_C = 125$ °C	38
Continuous Source Current (Diode Conduction) ^a	I_S	50	A
Pulsed Drain Current ^b	I_{DM}	200	
Single Pulse Avalanche Energy	I_{AS}	39	
Single Pulse Avalanche Current	E_{AS}	76	mJ
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C	71
		$T_C = 125$ °C	23
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	50	°C/W
Junction-to-Case (Drain)	R_{thJC}	2.1	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5	2.0	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 30 V	-	-	1.0	μA
		V _{GS} = 0 V, V _{DS} = 30 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V, V _{DS} = 30 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V, V _{DS} ≥ 5 V	50	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A	-	0.006	0.009	Ω
		V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C	-	-	0.014	
		V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C	-	-	0.017	
		V _{GS} = 4.5 V, I _D = 15 A	-	0.0087	0.012	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A	-	47	-	S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 15 V, f = 1 MHz	-	2306	2885	pF
Output Capacitance	C _{oss}		-	570	715	
Reverse Transfer Capacitance	C _{rss}		-	245	310	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V, V _{DS} = 15 V, I _D = 62 A	-	39.5	60	nC
Gate-Source Charge ^c	Q _{gs}		-	6.4	-	
Gate-Drain Charge ^c	Q _{gd}		-	6	-	
Gate Resistance	R _g	f = 1 MHz	1	1.9	2.8	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 1 Ω I _D ≅ 62 A, V _{GEN} = 10 V, R _g = 1 Ω	-	10	15	ns
Rise Time ^c	t _r		-	10	15	
Turn-Off Delay Time ^c	t _{d(off)}		-	22	33	
Fall Time ^c	t _f		-	8	12	
Source-Drain Diode Ratings and Characteristics^b						
Pulsed Current ^a	I _{SM}		-	-	200	A
Forward Voltage	V _{SD}	I _F = 18 A, V _{GS} = 0 V	-	0.85	1.2	V

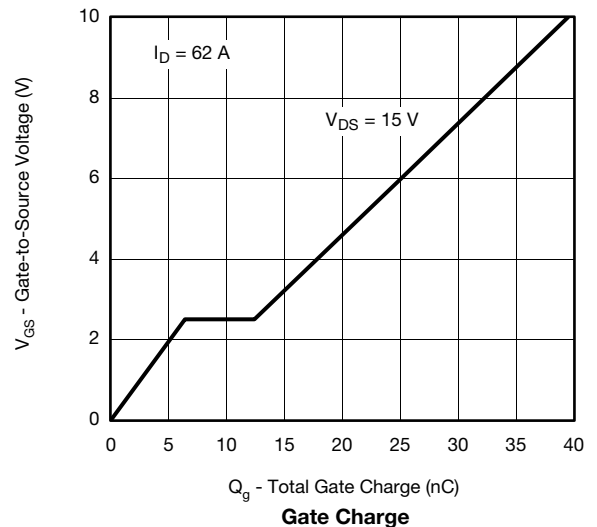
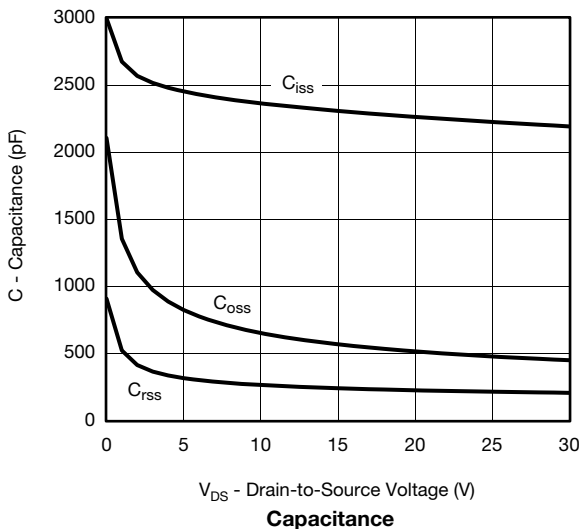
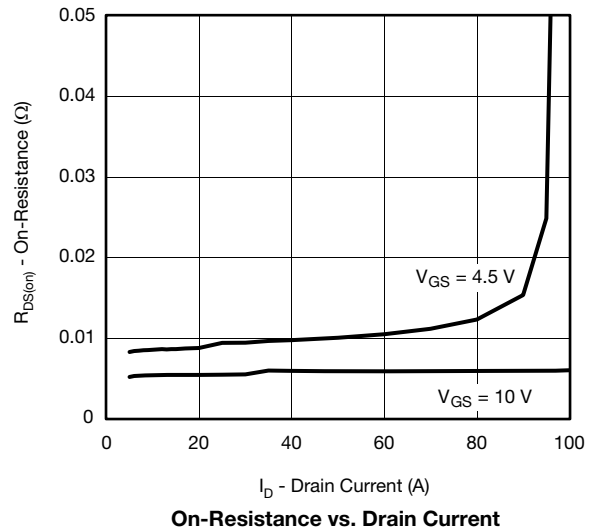
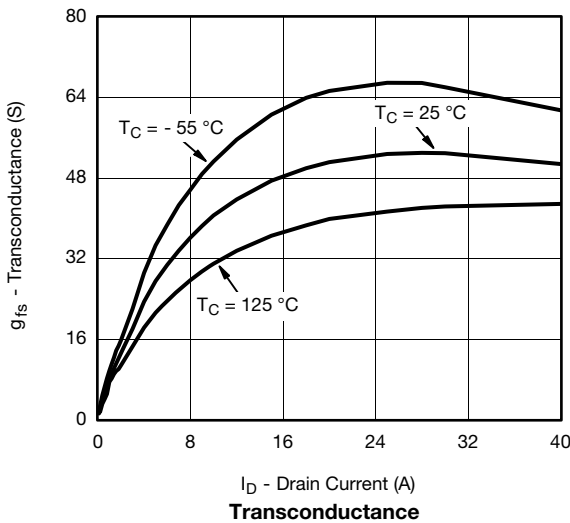
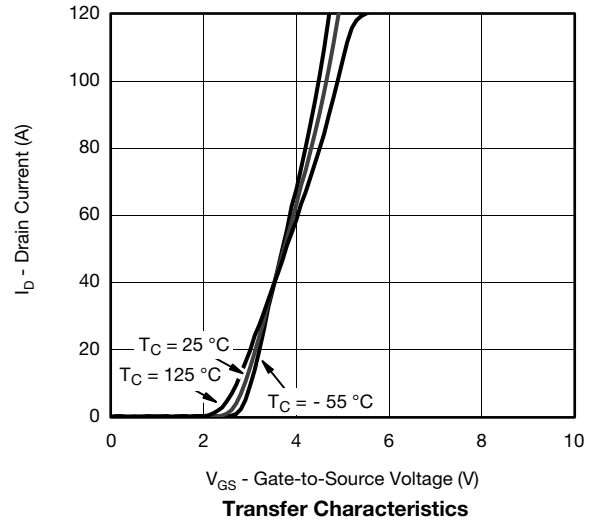
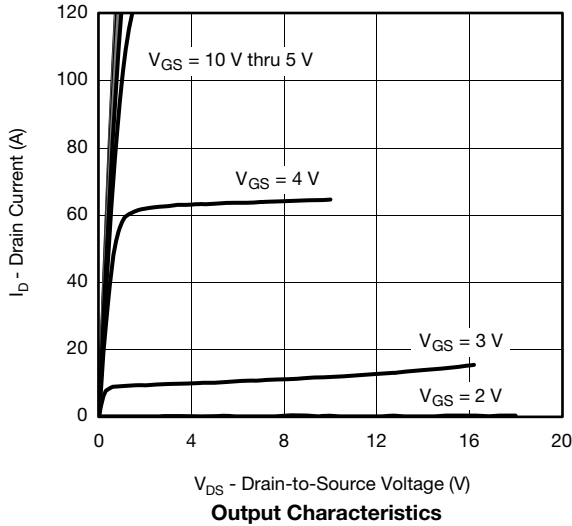
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

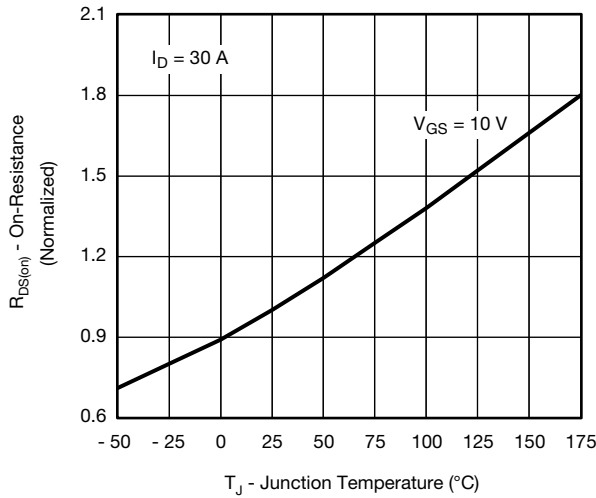


TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

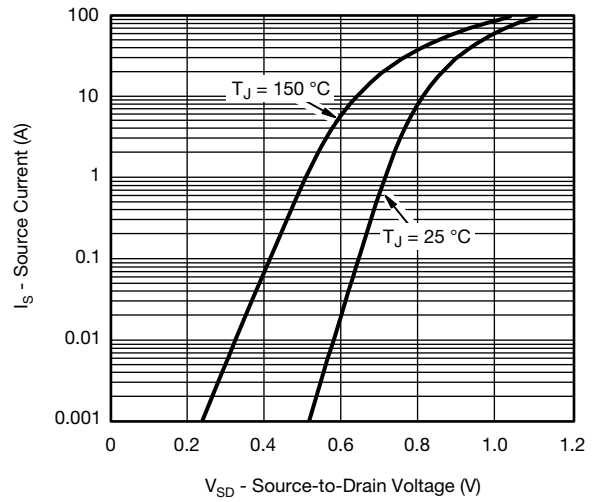




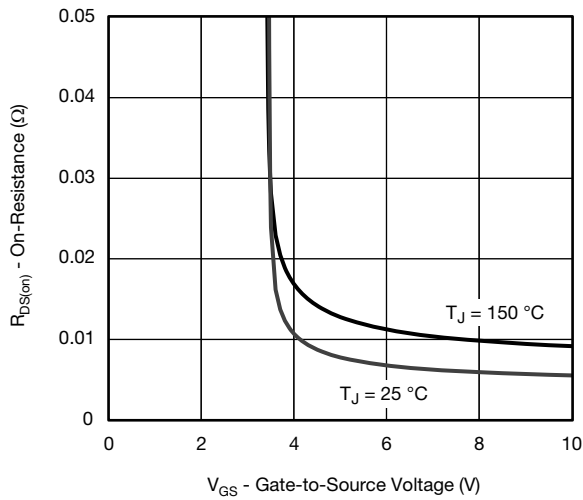
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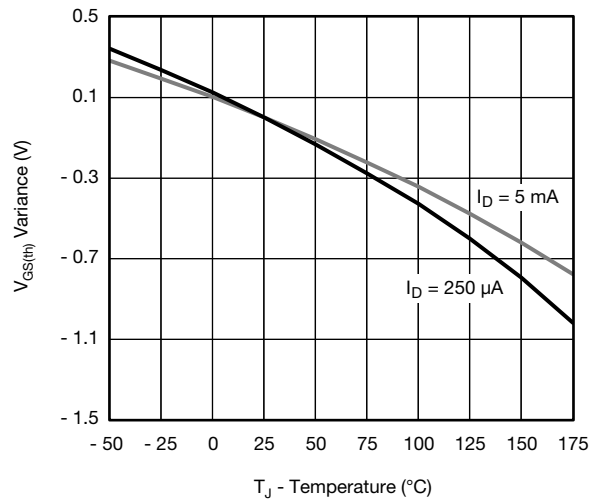
On-Resistance vs. Junction Temperature



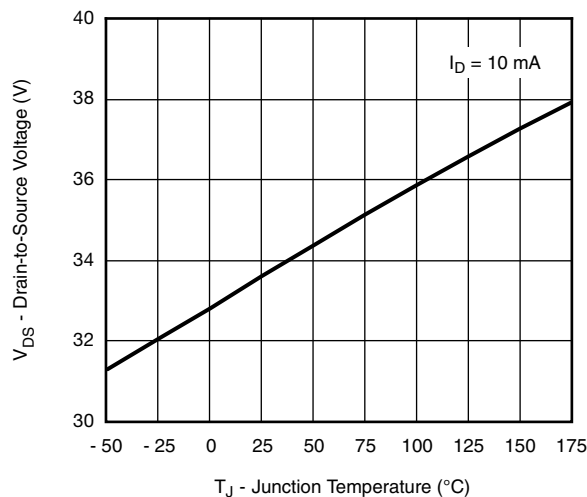
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



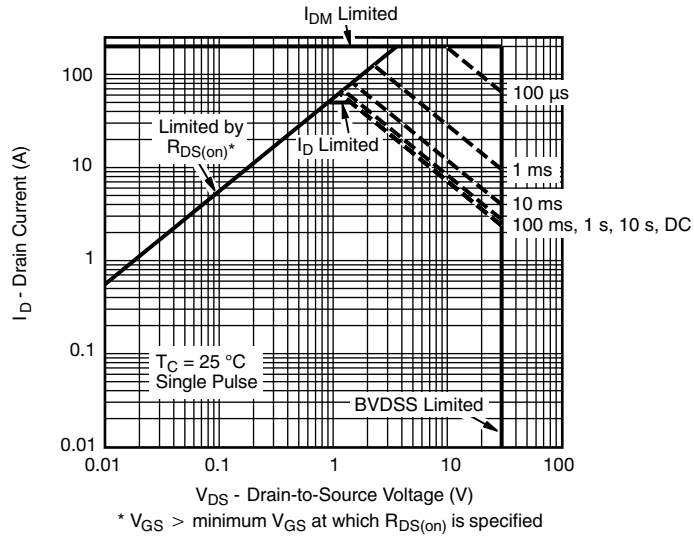
Threshold Voltage



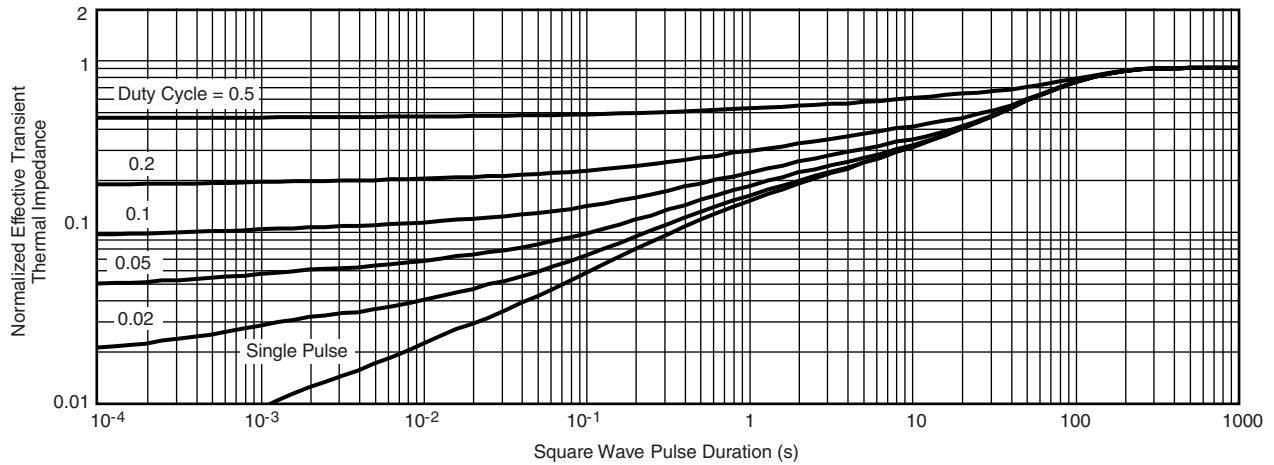
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



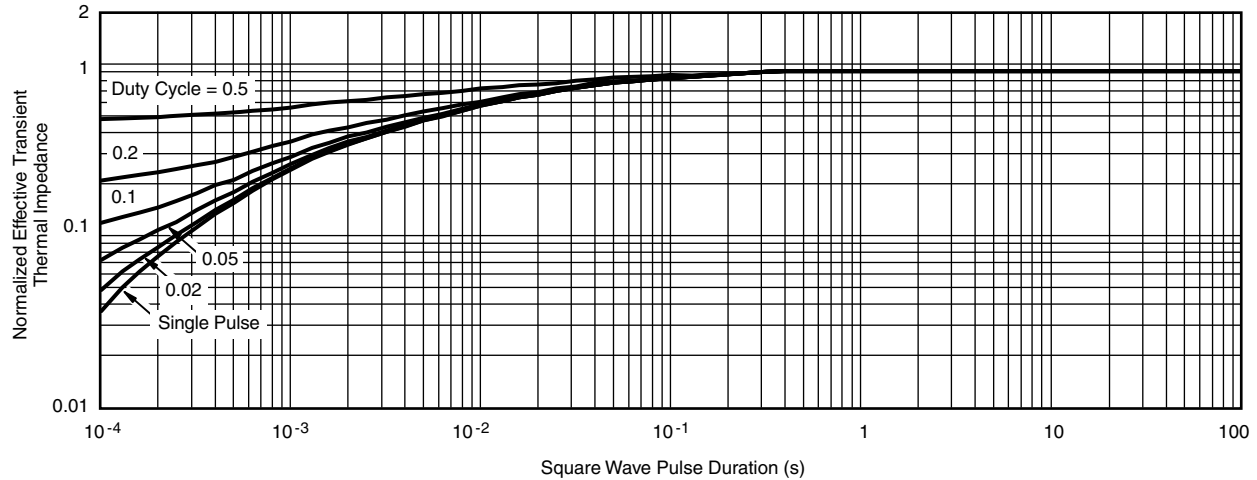
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-252AA Case Outline

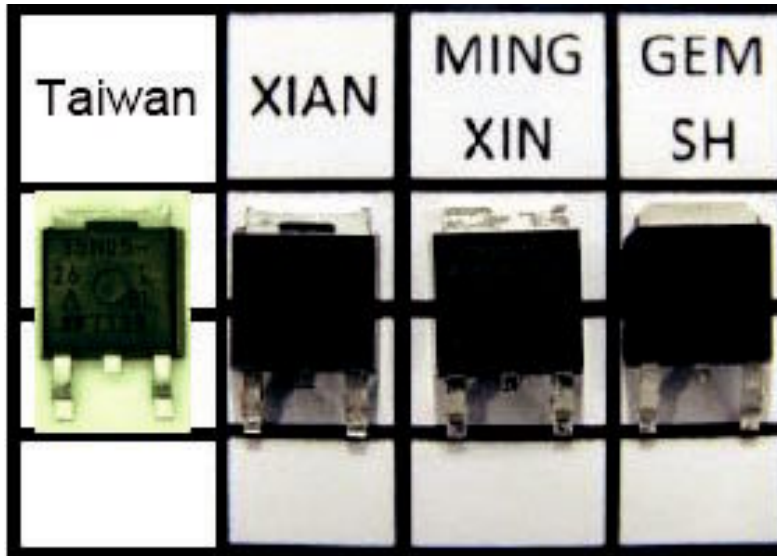


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060

ECN: T13-0359-Rev. O, 03-Jun-13
DWG: 5347

Notes

- Dimension L3 is for reference only.
- Xi'an, Mingxin, and GEM SH actual photo.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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